

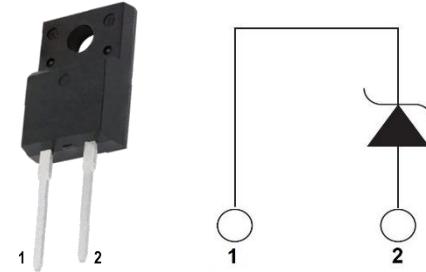


## Features

- Zero Forward/Reverse Recovery Current
- High Blocking Voltage
- High Frequency Operation
- Positive Temperature Coefficient on  $V_F$
- Temperature Independent Switching Behavior
- Fully isolated package, 4000Vpk

$V_R = 650 \text{ V}$   
 $I_F = 10\text{A} (T_c=106^\circ\text{C})$   
 $Q_c = 23\text{nC} (V_R=400\text{V})$

ITO-220AC



## Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- Higher Temperature Application
- No Switching loss
- Hard Switching & Higher Reliability
- Environmental Protection

## Applications

- PFC Boost Converters
- Chargers
- AC/DC Converters
- DC/DC Converters

Part Number	Package	Marking
LGE3D10065AF	ITO-220AC	LGE3D10065AF

## Maximum Ratings ( $T_c=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Value	Unit
Peak Repetitive Reverse Voltage	$V_{RRM}$		650	V
Peak Reverse Surge Voltage	$V_{RSM}$		650	V
DC Blocking Voltage	$V_R$		650	V
Continuous Forward Current	$I_F$	$T_c=25^\circ\text{C}$ $T_c=95^\circ\text{C}$ $T_c=106^\circ\text{C}$ $T_c=135^\circ\text{C}$	16 11 10 7	A
Non repetitive Forward Surge Current	$I_{FSM}$	$T_c = 25^\circ\text{C}, t_p=10 \text{ ms},$ Half Sine Pulse $T_c = 110^\circ\text{C}, t_p=10 \text{ ms},$ Half Sine Pulse $T_c = 25^\circ\text{C}, t_p=10 \mu\text{s}$	50 45 400	A
Repetitive peak Forward Surge Current	$I_{FRM}$	$T_c = 25^\circ\text{C}, t_p=10 \text{ ms},$ Freq = 0.1Hz, 100 cycles, Half Sine Pulse $T_c = 110^\circ\text{C}, t_p=10 \text{ ms},$ Freq = 0.1Hz, 100 cycles, Half Sine Pulse	45 40	A
Total power dissipation	$P_D$	$T_c=25^\circ\text{C}$	38	W
Operating Junction Temperature	$T_J$		-55 to 175	°C
Storage Temperature	$T_{STG}$		-55 to 175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



## Electrical Characteristics

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
DC Blocking Voltage	$V_{DC}$	$I_R = 250\mu A, T_J = 25^\circ C$	650			V
Forward Voltage	$V_F$	$I_F = 10A, T_J = 25^\circ C$		1.4	1.75	V
		$I_F = 10A, T_J = 125^\circ C$		1.5		
		$I_F = 10A, T_J = 175^\circ C$		1.7		V
Reverse Current	$I_R$	$V_R = 650V, T_J = 25^\circ C$		2	50	uA
		$V_R = 650V, T_J = 125^\circ C$		6		uA
		$V_R = 650V, T_J = 175^\circ C$		18		uA
Total Capacitive Charge	$Q_C$	$V_R = 400V$ $T_J = 25^\circ C$		23		nC
Total Capacitance	C	$V_R = 1V, T_J = 25^\circ C,$ Freq = 1MHz		395		
		$V_R = 200V, T_J = 25^\circ C,$ Freq = 1MHz		43		pF
		$V_R = 400V, T_J = 25^\circ C,$ Freq = 1MHz		32		

Note: This is a majority carrier diode, so there is no reverse recovery charge

## Thermal Characteristics

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Thermal Resistance	$R_{th(j-c)}$	Junction to case		3.3	4.0	°C/W
	$R_{th(j-a)}$	Junction to ambient		57		



## Typical Electrical Curves

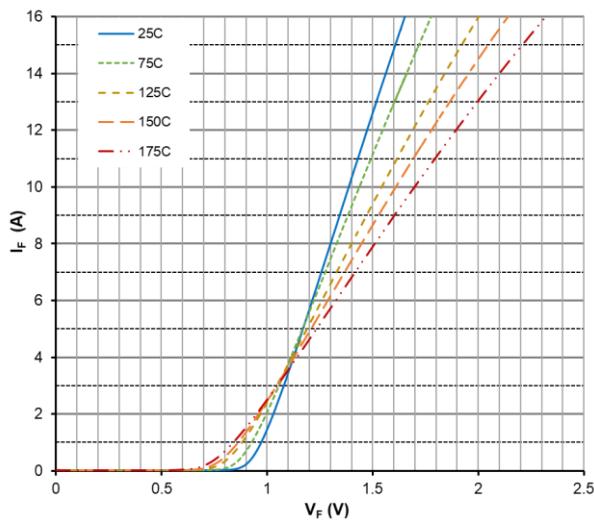


Figure 1. Forward Characteristics

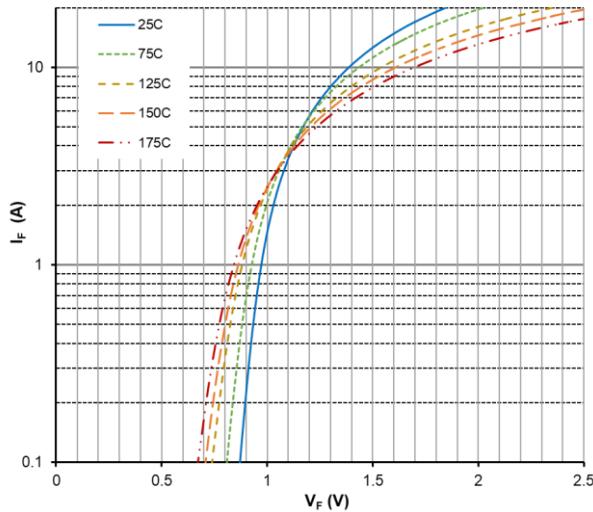


Figure 2. Forward Characteristics

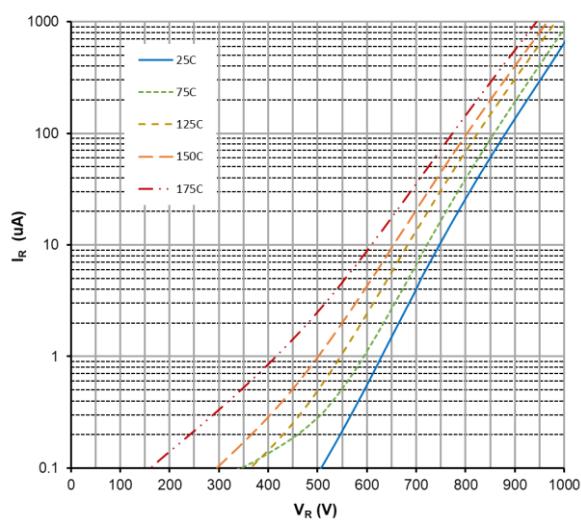


Figure 3. Reverse Characteristics

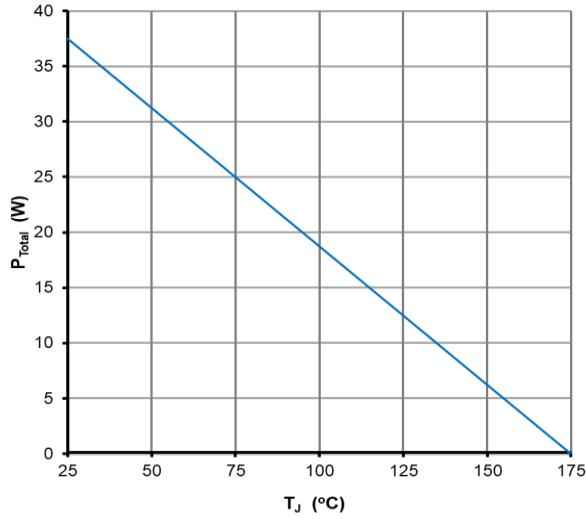


Figure 4. Power Derating

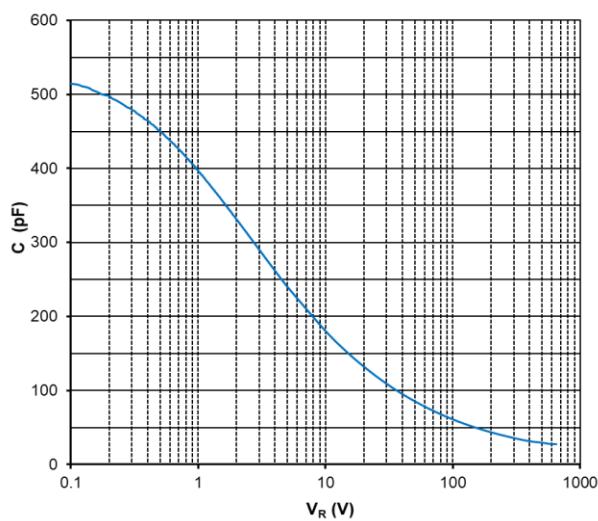


Figure 5. Capacitance vs Reverse Voltage

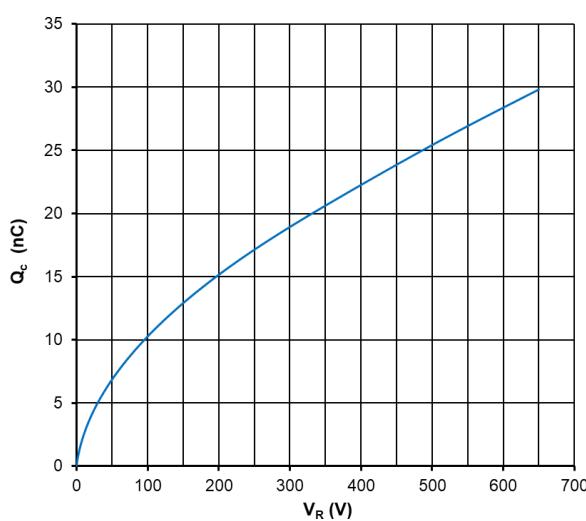
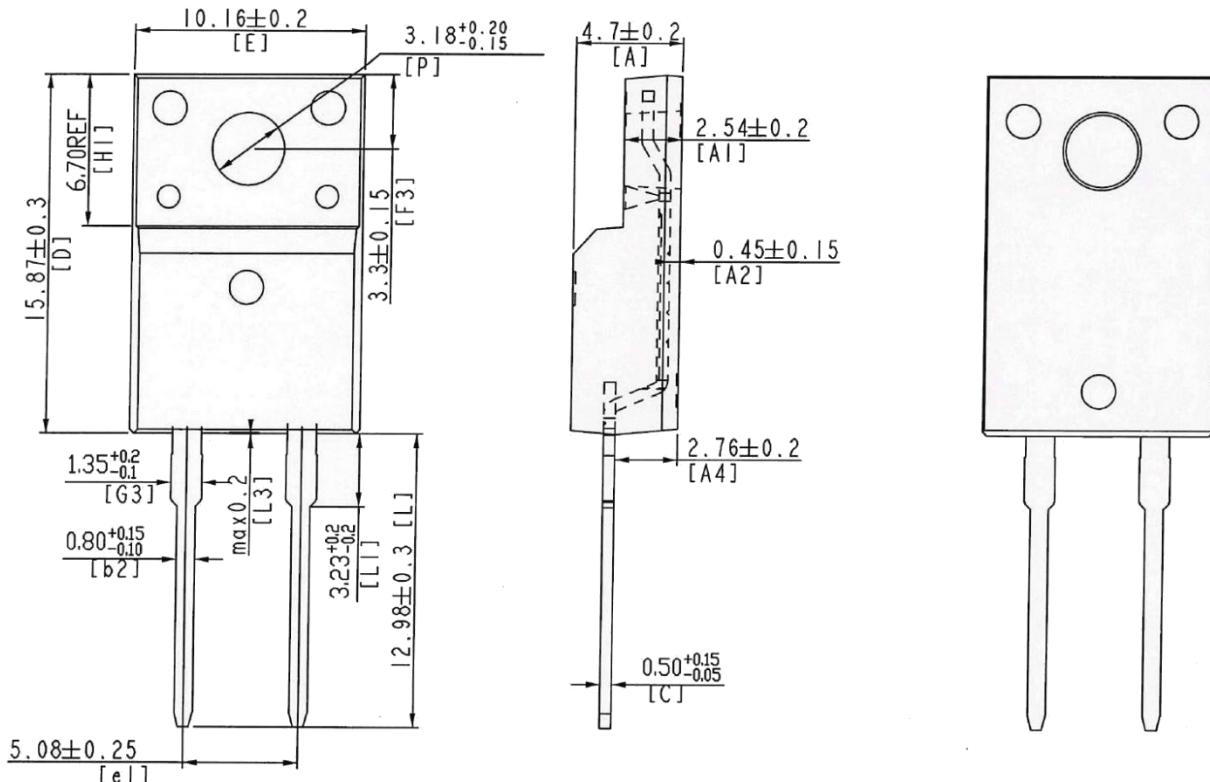


Figure 6. Recovery Charge vs Reverse Voltage



## Package Dimensions

(TO-220-2 FullPAK)



Part Number	Package	Packing	Marking
LGE3D10065AF	TO-220-2 FullPAK	50pcs / Tube	LGE3D10065AF